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(54) **SEMICONDUCTOR CHIP, METHOD FOR MANUFACTURING THE SAME, AND ELECTRONIC DEVICE**

(71) Applicant: **SONY SEMICONDUCTOR SOLUTIONS CORPORATION**, KANAGAWA (JP)

(72) Inventors: **RYOSUKE KAMATANI**, KANAGAWA (JP); **TOMIYUKI YUKAWA**, KANAGAWA (JP); **ATSUSHI YAMAMOTO**, KANAGAWA (JP)

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(57) **ABSTRACT**

The present technology relates to a semiconductor chip, a method for manufacturing the same, and an electronic device that can improve reliability and durability. The semiconductor chip includes a solid-state imaging element such as a complementary metal oxide semiconductor (CMOS) image sensor (CIS), a glass substrate provided on the solid-state imaging element, and a lens formed on the glass substrate. The glass substrate has a groove having a depth of L1-L2 around a region where the lens is formed. The present technology can be applied, for example, to a semiconductor chip or the like that is a wafer level chip size package (WCSP) having a solid-state imaging element such as a CIS.